

IN THE SPECIFICATION

Page 3, line 14:

In a preferred embodiment of the invention, a plurality of successive layers are firmly adhered to one another and to a wafer surface and an electrical component or sub-assembly even when the wafer surface is not even and the layers are bent. The wafer surface is initially cleaned by an ion bombardment of an inert gas (e.g. argon) on the wafer surface in an RF discharge at a relatively high gas pressure. The wafer surface is then provided with a microscopic roughness by applying a low power so that the inert gas (e.g. argon) ions do not have sufficient energy to etch the surface.

Pages 12-13, line 14

Pages 12-13, line 16:

Figure 5 is a curve 36 showing the relationship between RF bias power in watts along the horizontal axis and stress in E9 dynes per square centimeter along the vertical axis when the nickel vanadium layer 20 is deposited on the chromium layer 18. The curve 36 shown in Figure 5 is provided for deposition equipment such as the equipment shown in Figure 4. Figure 5 shows how the stress in the nickel-vanadium layer 20 decreases with increases in the RF power applied.